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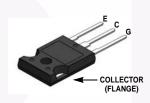
FGH15T120SMD 1200 V, 15 A Field Stop Trench IGBT

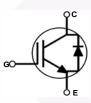
Features

- FS Trench Technology, Positive Temperature Coefficient
- High Speed Switching
- Low Saturation Voltage: V_{CE(sat)} =1.8 V @ I_C = 15 A
- 100% of The Parts Tested for ILM(1) ٠
- · High Input Impedance
- RoHS Compliant

Applications

• Solar Inverter, Welder, UPS & PFC Applications.





Using innovative field stop trench IGBT technology, Fairchild's

new series of field stop trench IGBTs offer the optimum

performance for hard switching application such as solar

inverter, UPS, welder and PFC applications.

General Description

Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description		Ratings	Unit	
V _{CES}	Collector to Emitter Voltage		1200	V	
V _{GES}	Gate to Emitter Voltage		±25	V	
	Transient Gate to Emitter Voltage		±30	V	
L.	Collector Current	@ T _C = 25°C	30	A	
I _C	Collector Current	@ T _C = 100 ^o C	15	A	
I _{LM} (1)	Clamped Inductive Load Current	@ T _C = 25°C	60	A	
I _{CM} (2)	Pulsed Collector Current		60	A	
I _F	Diode Continuous Forward Current	@ T _C = 25°C	30	A	
	Diode Continuous Forward Current	@ T _C = 100°C	15	A	
I _{FM}	Diode Maximum Forward Current		100	A	
P _D	Maximum Power Dissipation	@ T _C = 25°C	333	W	
	Maximum Power Dissipation	@ T _C = 100 ^o C	167	W	
TJ	Operating Junction Temperature		-55 to +175	°C	
T _{stg}	Storage Temperature Range		-55 to +175	°C	
TL	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300	°C	

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
R _{0JC} (IGBT) Thermal Resistance, Junction to Case			0.45	°C/W
R _{0JC} (Diode) Thermal Resistance, Junction to Case			2.0	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient		40	°C/W

Notes:

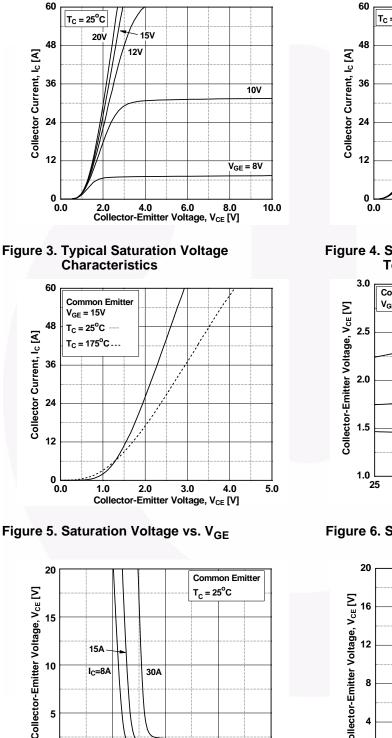
1. Vcc = 600 V,V_{GE} = 15 V, I_C = 60 A, R_G = 34 \odot . Inductive Load 2. Limited by Tjmax

Device MarkingDeviceFGH15T120SMDFGH15T120SMD_F155		Device	Package	Reel Size	Таре	Tape Width		Quantity	
		TO-247G03	-		-	30			
Electric	al Cha	racteristics of the l	GBT T _C = 25°C	unless otherwise noted					
Symbol	ol Parameter		Test Co	onditions	Min.	Тур.	Max.	Unit	
Off Charac	teristics								
BV _{CES}	1	to Emitter Breakdown Voltage	V _{GE} = 0 V, I _C = 250 uA		1200	-	-	V	
ICES		Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0 V$		-	-	250	uA	
I _{GES}	G-E Leak	age Current	$V_{GE} = V_{GES}, V_{CE} = 0 V$		-	-	±400	nA	
GLO		0	GE GES, CE O						
On Charac	teristics								
V _{GE(th)}	G-E Thre	shold Voltage	$I_{\rm C}$ = 15 mA, V _C	-	4.9	6.2	7.5	V	
	Collector to Emitter Saturation Voltage		$I_{C} = 15 \text{ A}, V_{GE} = 15 \text{ V}$ $T_{C} = 25^{\circ}\text{C}$		-	1.8	2.4	V	
V _{CE(sat)}			I _C = 15 A, V _{GE} T _C = 175 ^o C	= 15 V,	-	1.9	-	V	
Dynamic C	haracteris	tics							
C _{ies}	Input Cap		V _{CE} = 30 V, V _{GE} = 0 V, f = 1MHz		-	1460	-	pF	
C _{oes}	Output Ca	apacitance			-	65	-	pF	
C _{res}	-	Transfer Capacitance			-	37	-	pF	
Switching	Character	istics							
t _{d(on)}	1	Delay Time	V _{CC} = 600 V, I _C = 15 A,		-	32	-	ns	
t _r	Rise Time	9			-	47	-	ns	
t _{d(off)}	Turn-Off I	Delay Time			-	490	-	ns	
t _f	Fall Time		$R_G = 34 \Omega, V_{GI}$	= 15 V,	-	12	-	ns	
E _{on}	Turn-On S	Switching Loss	Inductive Load	$T_{C} = 25^{\circ}C$	-	1.15	-	mJ	
E _{off}	Turn-Off S	Switching Loss	-		-	0.46	-	mJ	
E _{ts}	Total Swit	ching Loss			-	1.61	-	mJ	
t _{d(on)}	Turn-On I	Delay Time				32	-	ns	
t _r	Rise Time		1	-	-	42	-	ns	
t _{d(off)}	Turn-Off I	Delay Time	V _{CC} = 600 V, I _C	• = 15 A,	-	510	-	ns	
t _f	Fall Time		$R_G = 34 \Omega$, $V_{GE} = 15 V$, Inductive Load, $T_C = 175^{\circ}C$		-	24	-	ns	
E _{on}	Turn-On S	Switching Loss			-	1.86	-	mJ	
E _{off}	Turn-Off S	Switching Loss			-	0.70		mJ	
E _{ts}	Total Swit	ching Loss			-	2.56	- (mJ	
Qg	Total Gate	e Charge			-	128		nC	
Q _{ge}		mitter Charge	$V_{CE} = 600 \text{ V}, I_{C}$; = 15 A,	-	11	-	nC	
Q _{gc}		collector Charge	V _{GE} = 15 V		-	70	-	nC	

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V _{FM}	Diode Forward Voltage	I _F = 15 A, T _C = 25 ^o C	-	2.8	3.7	V
		I _F = 15 A, T _C = 175°C	-	2.3	-	V
t _{rr}	Diode Reverse Recovery Time	$V_R = 600 \text{ V}, I_F = 15 \text{ A},$ di _F /dt = 200 A/us, $T_C = 25^{\circ}\text{C}$	-	72	-	ns
I _{rr}	Diode Peak Reverse Recovery Current		-	7.4	-	А
Q _{rr}	Diode Reverse Recovery Charge		-	270	-	nC
E _{rec}	Reverse Recovery Energy	V _R = 600 V, I _F = 15 A,	-	120	-	uJ
t _{rr}	Diode Reverse Recovery Time	$di_{\rm F}/dt = 200 \text{ A/us}, \ T_{\rm C} = 175^{\rm o}{\rm C}$	-	183	-	ns
I _{rr}	Diode Peak Reverse Recovery Current		-	12	-	А
Q _{rr}	Diode Reverse Recovery Charge	1	-	1085	-	nC

Electrical Characteristics of the DIODE T_c = 25°C unless otherwise noted

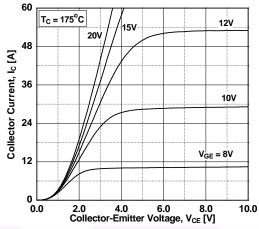
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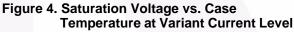


Typical Performance Characteristics

Figure 1. Typical Output Characteristics

Figure 2. Typical Output Characteristics





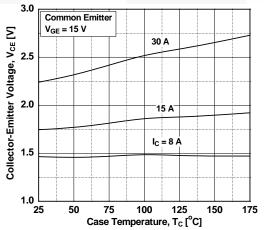
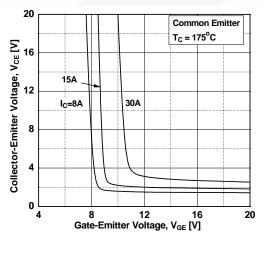


Figure 6. Saturation Voltage vs. V_{GE}



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I_C=8A

30A

8 12 16 Gate-Emitter Voltage, V_{GE} [V]

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FGH15T120SMD — 1200 V, 15 A Field Stop Trench IGBT

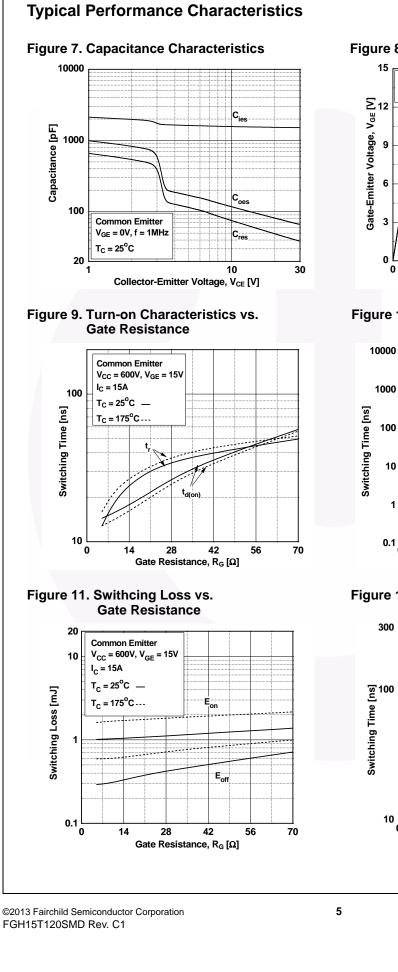
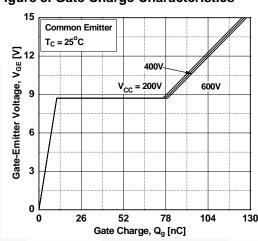


Figure 8. Gate Charge Characteristics





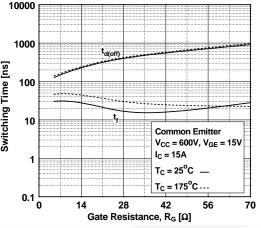
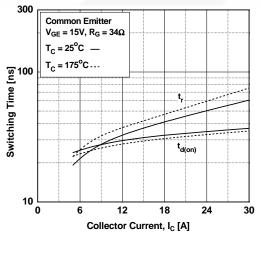
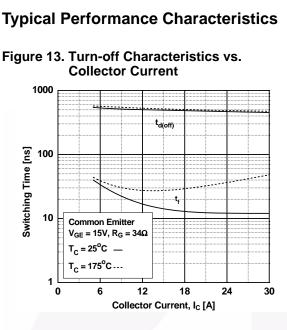
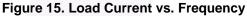
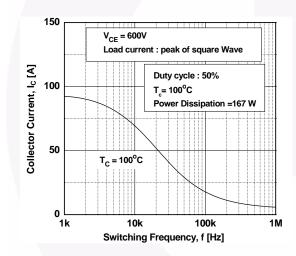


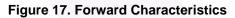
Figure 12. Turn-on Characteristics vs. Collector Current

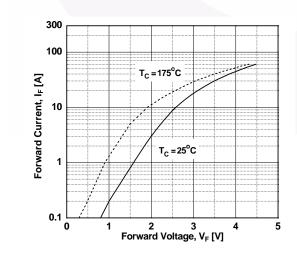


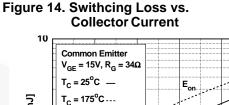


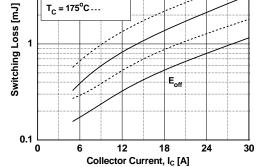














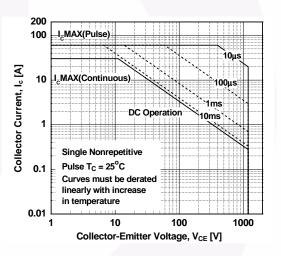
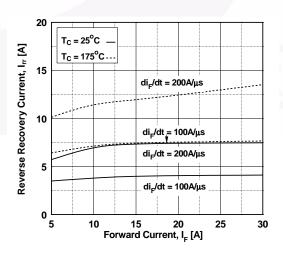
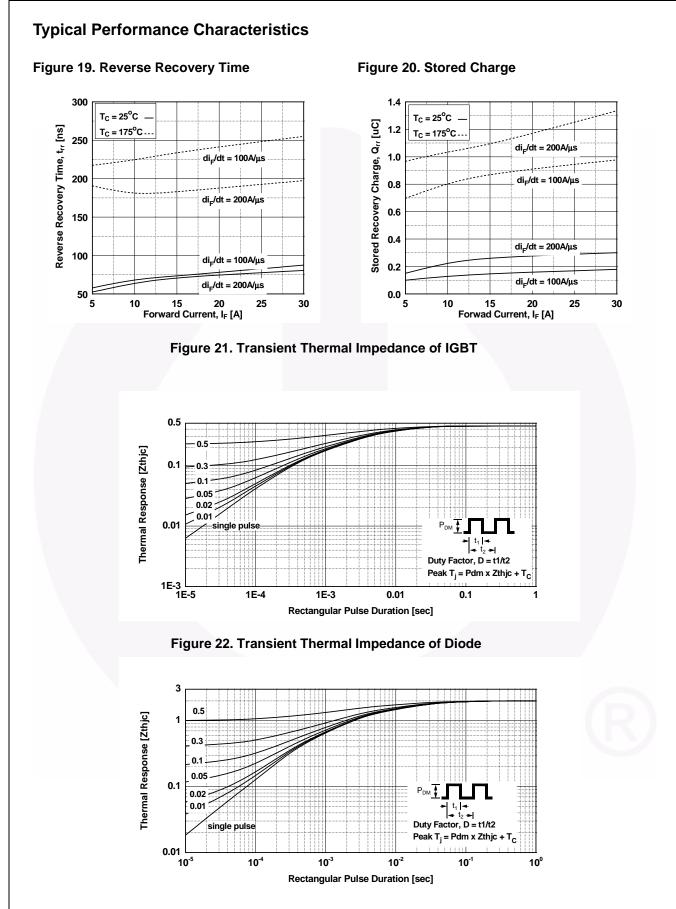
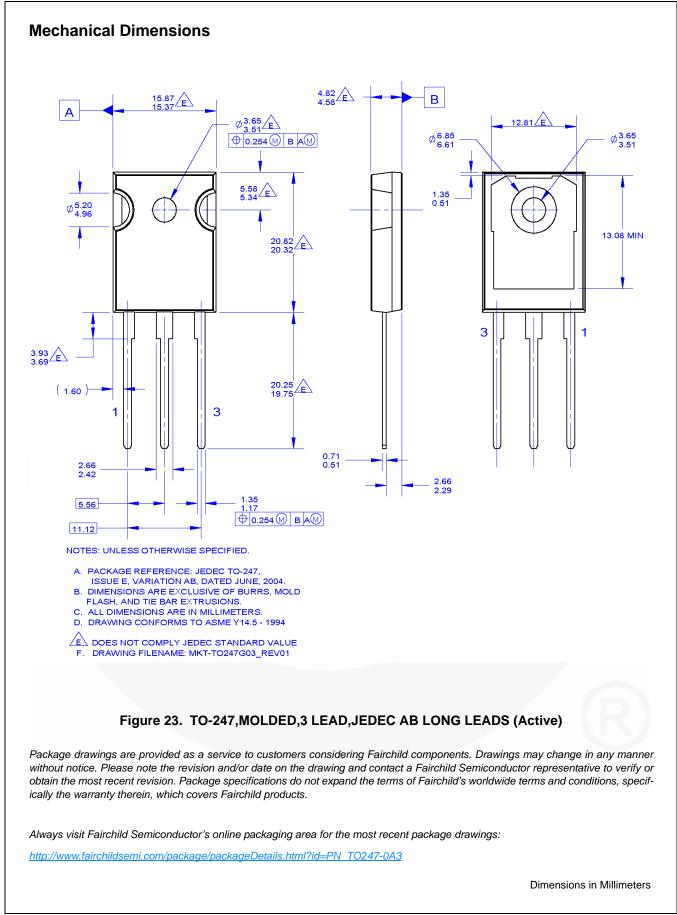


Figure 18. Reverse Recovery Current









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